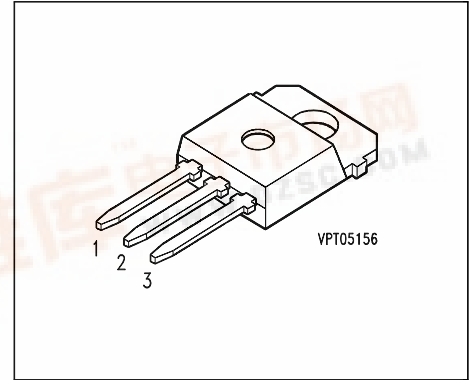


### SIPMOS<sup>®</sup> Power Transistor

- N channel
- Enhancement mode
- Avalanche-rated



Pin 1	Pin 2	Pin 3
G	D	S

Type	V <sub>DS</sub>	I <sub>D</sub>	R <sub>DS(on)</sub>	Package	Ordering Code
BUZ 325	400 V	12.5 A	0.35 Ω	TO-218 AA	C67078-S3118-A2

### Maximum Ratings

Parameter	Symbol	Values	Unit
Continuous drain current <i>T<sub>C</sub></i> = 27 °C	I <sub>D</sub>	12.5	A
Pulsed drain current <i>T<sub>C</sub></i> = 25 °C	I <sub>Dpuls</sub>	50	A
Avalanche current, limited by <i>T<sub>jmax</sub></i>	I <sub>AR</sub>	12.5	A
Avalanche energy, periodic limited by <i>T<sub>jmax</sub></i>	E <sub>AR</sub>	13	mJ
Avalanche energy, single pulse I <sub>D</sub> = 12.5 A, V <sub>DD</sub> = 50 V, R <sub>GS</sub> = 25 Ω L = 7.5 mH, <i>T<sub>j</sub></i> = 25 °C	E <sub>AS</sub>	670	mJ
Gate source voltage	V <sub>GS</sub>	± 20	V
Power dissipation <i>T<sub>C</sub></i> = 25 °C	P <sub>tot</sub>	125	W
Operating temperature	<i>T<sub>j</sub></i>	-55 ... + 150	°C
Storage temperature	<i>T<sub>stg</sub></i>	-55 ... + 150	°C
Thermal resistance, chip case	R <sub>thJC</sub>	≤ 1	K/W
Thermal resistance, chip to ambient	R <sub>thJA</sub>	75	K/W
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		55 / 150 / 56	



**Electrical Characteristics**, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Static Characteristics</b>					
Drain- source breakdown voltage $V_{GS} = 0\text{ V}, I_D = 0.25\text{ mA}, T_j = 25\text{ }^\circ\text{C}$	$V_{(BR)DSS}$	400	-	-	V
Gate threshold voltage $V_{GS}=V_{DS}, I_D = 1\text{ mA}$	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current $V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_j = 25\text{ }^\circ\text{C}$ $V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_j = 125\text{ }^\circ\text{C}$	$I_{DSS}$	-	0.1 10	1 100	$\mu\text{A}$
Gate-source leakage current $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	$I_{GSS}$	-	10	100	nA
Drain-Source on-resistance $V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	$R_{DS(on)}$	-	0.28	0.35	$\Omega$

**Electrical Characteristics**, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Dynamic Characteristics</b>					
Transconductance $V_{DS} \geq 2 * I_D * R_{DS(on)max}$ , $I_D = 8 \text{ A}$	$g_{fs}$	8	9.8	-	S
Input capacitance $V_{GS} = 0 \text{ V}$ , $V_{DS} = 25 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{iss}$	-	1900	2500	pF
Output capacitance $V_{GS} = 0 \text{ V}$ , $V_{DS} = 25 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{oss}$	-	260	400	
Reverse transfer capacitance $V_{GS} = 0 \text{ V}$ , $V_{DS} = 25 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{rss}$	-	110	170	
Turn-on delay time $V_{DD} = 30 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$	$t_{d(on)}$	-	30	45	ns
Rise time $V_{DD} = 30 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$	$t_r$	-	90	135	
Turn-off delay time $V_{DD} = 30 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$	$t_{d(off)}$	-	350	465	
Fall time $V_{DD} = 30 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$	$t_f$	-	100	135	

**Electrical Characteristics, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified**

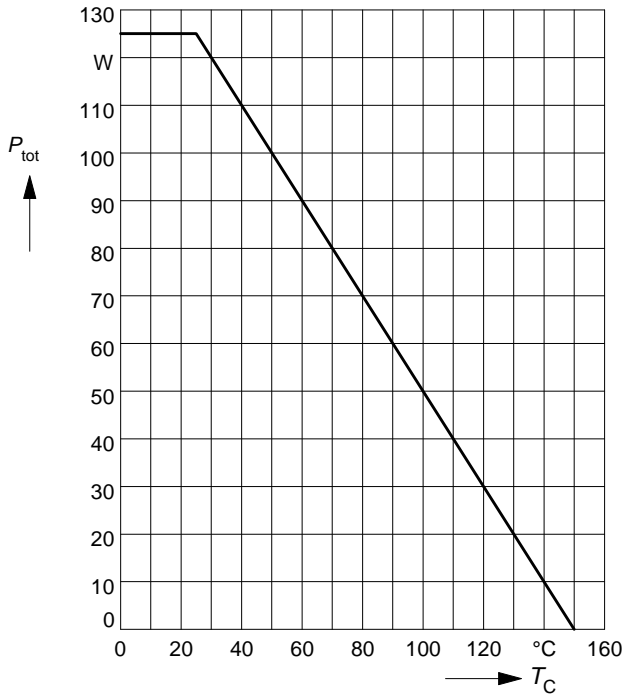
Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**Reverse Diode**

Inverse diode continuous forward current $T_C = 25^\circ\text{C}$	$I_S$	-	-	12.5	A
Inverse diode direct current,pulsed $T_C = 25^\circ\text{C}$	$I_{SM}$	-	-	50	
Inverse diode forward voltage $V_{GS} = 0\text{ V}, I_F = 25\text{ A}$	$V_{SD}$	-	1	1.5	V
Reverse recovery time $V_R = 100\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	$t_{rr}$	-	450	-	ns
Reverse recovery charge $V_R = 100\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	$Q_{rr}$	-	6.8	-	$\mu\text{C}$

### Power dissipation

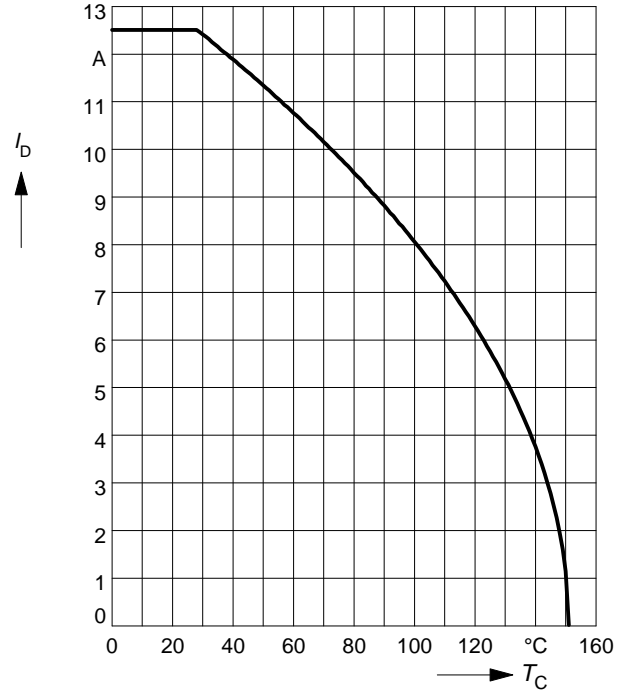
$$P_{tot} = f(T_C)$$



### Drain current

$$I_D = f(T_C)$$

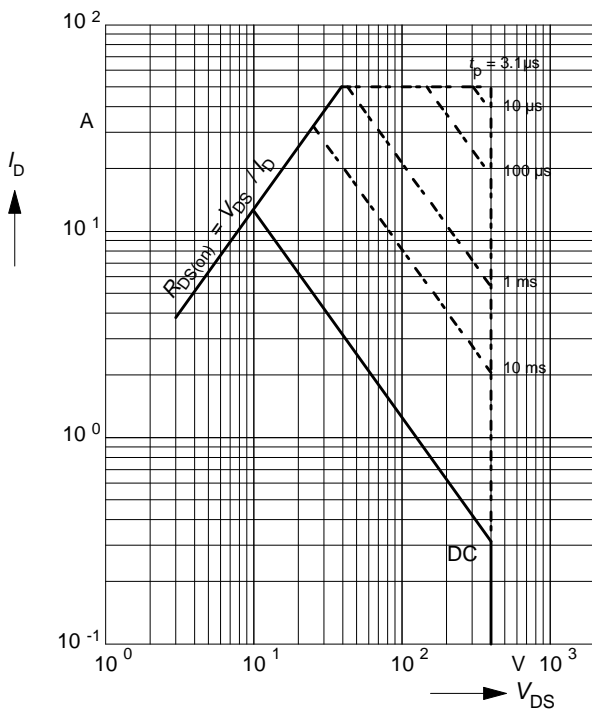
parameter:  $V_{GS} \geq 10$  V



### Safe operating area

$$I_D = f(V_{DS})$$

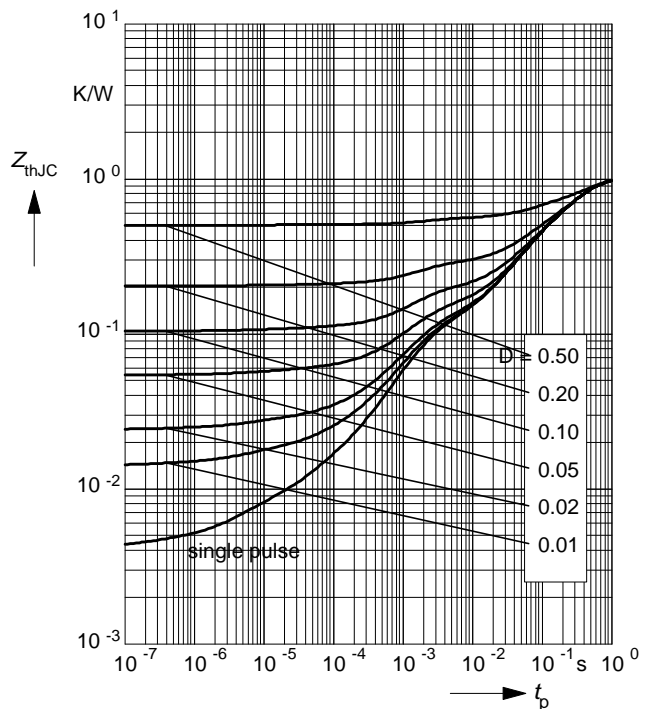
parameter:  $D = 0.01$ ,  $T_C = 25^\circ\text{C}$



### Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

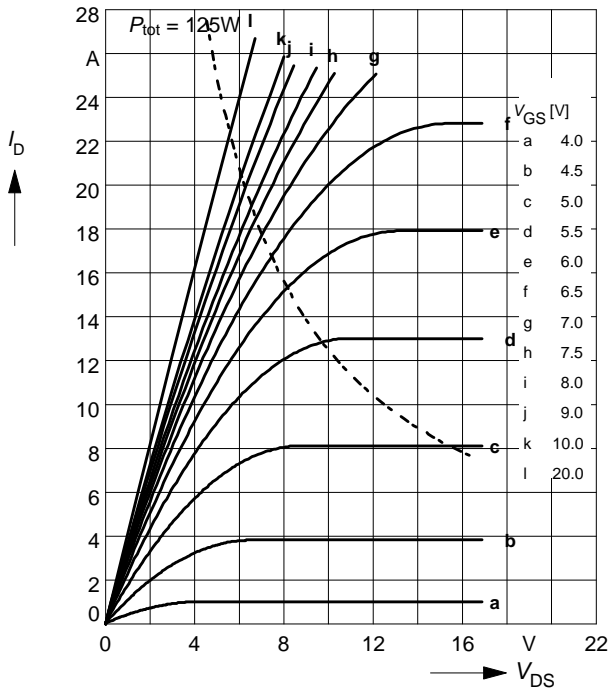
parameter:  $D = t_p / T$



### Typ. output characteristics

$$I_D = f(V_{DS})$$

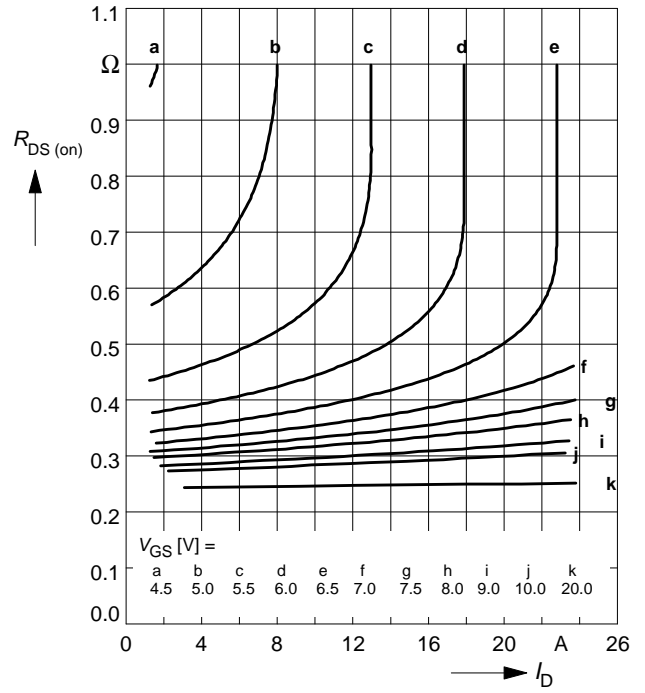
parameter:  $t_p = 80 \mu s$



### Typ. drain-source on-resistance

$$R_{DS(on)} = f(I_D)$$

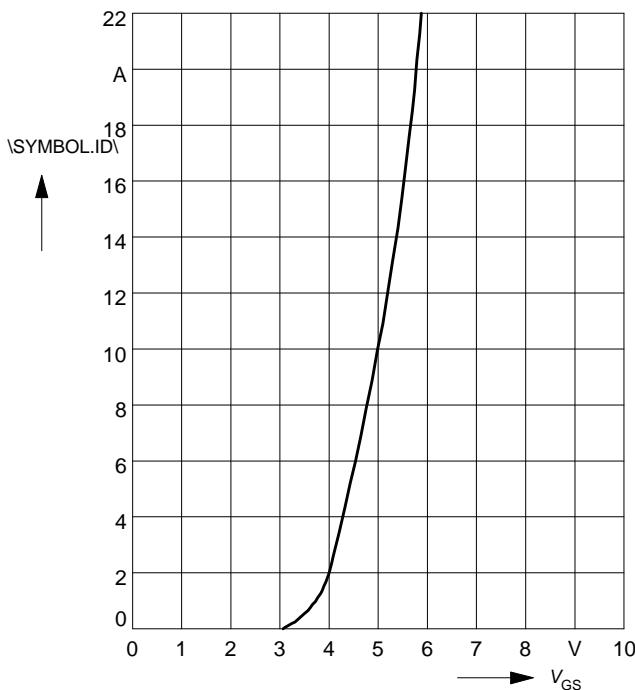
parameter:  $V_{GS}$



### Typ. transfer characteristics $I_D = f(V_{GS})$

parameter:  $t_p = 80 \mu s$

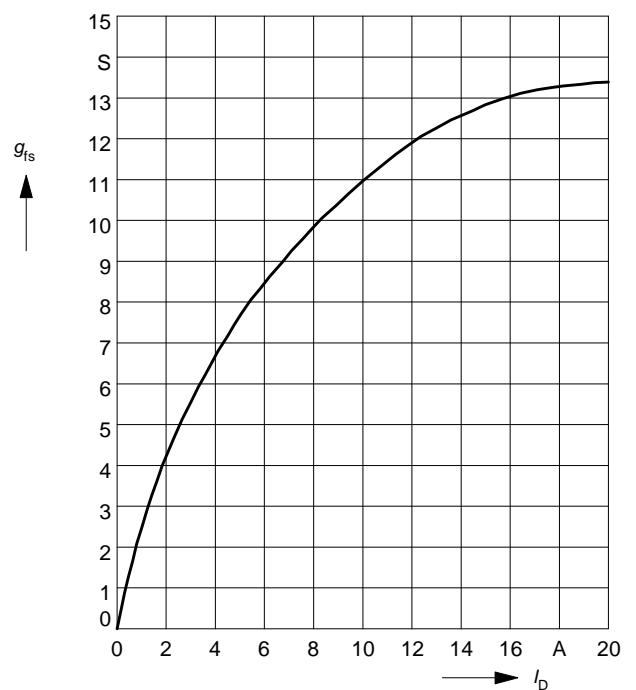
$$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$



### Typ. forward transconductance $g_{fs} = f(I_D)$

parameter:  $t_p = 80 \mu s$ ,

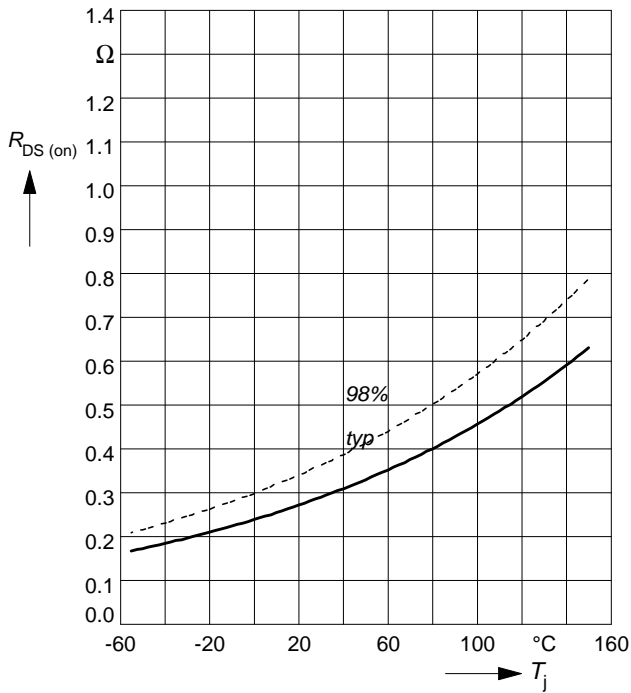
$$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$



### Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

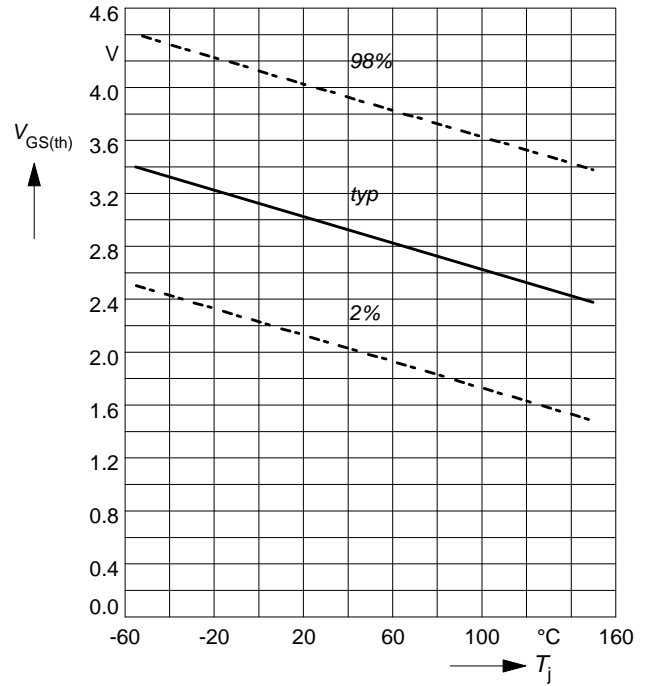
parameter:  $I_D = 8\text{ A}$ ,  $V_{GS} = 10\text{ V}$



### Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

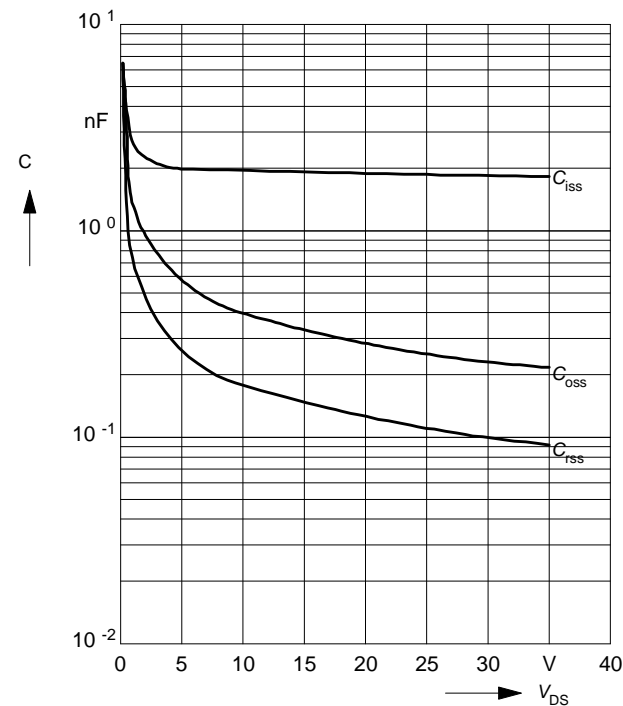
parameter:  $V_{GS} = V_{DS}$ ,  $I_D = 1\text{ mA}$



### Typ. capacitances

$$C = f(V_{DS})$$

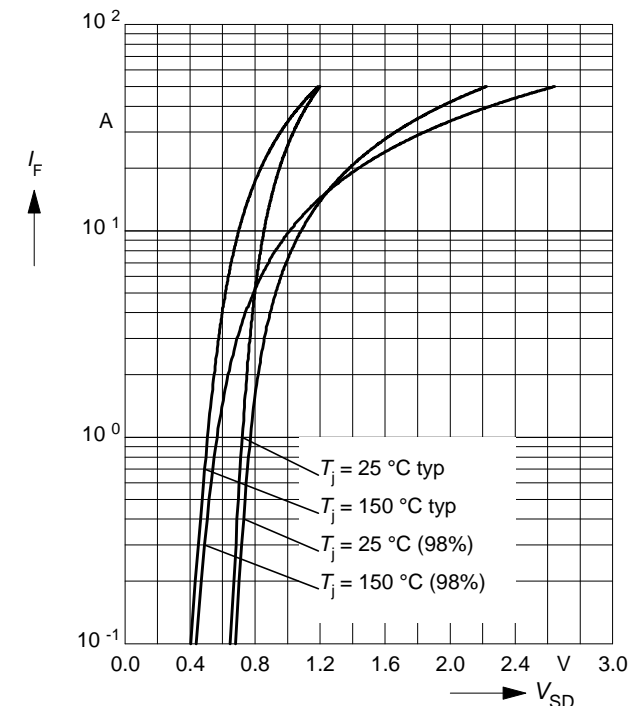
parameter:  $V_{GS} = 0\text{ V}$ ,  $f = 1\text{ MHz}$



### Forward characteristics of reverse diode

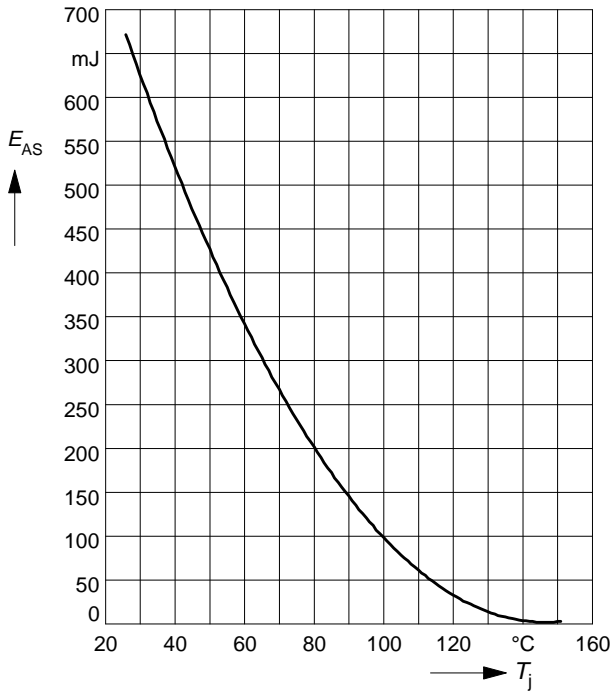
$$I_F = f(V_{SD})$$

parameter:  $T_j$ ,  $t_p = 80\text{ }\mu\text{s}$



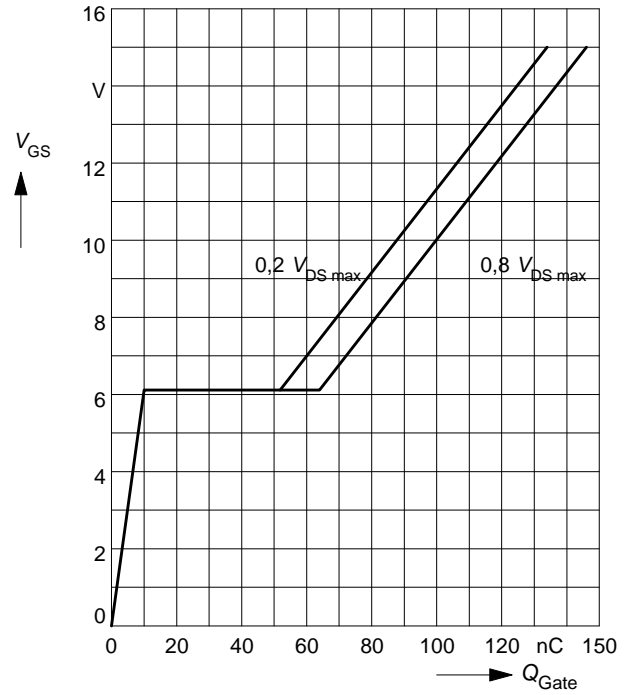
### Avalanche energy $E_{AS} = f(T_j)$

parameter:  $I_D = 12.5 \text{ A}$ ,  $V_{DD} = 50 \text{ V}$   
 $R_{GS} = 25 \Omega$ ,  $L = 7.5 \text{ mH}$



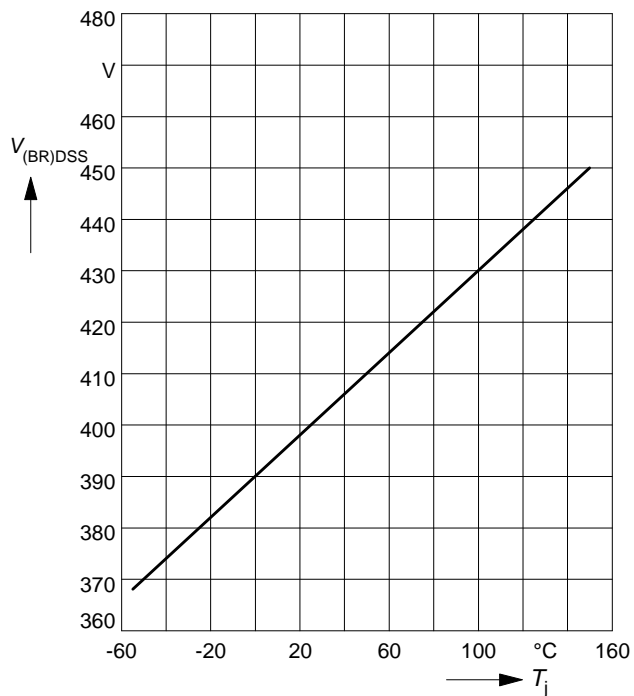
### Typ. gate charge $V_{GS} = f(Q_{Gate})$

parameter:  $I_{D \text{ puls}} = 21 \text{ A}$



### Drain-source breakdown voltage $V_{(BR)DSS} = f(T_j)$

$V_{(BR)DSS} = f(T_j)$

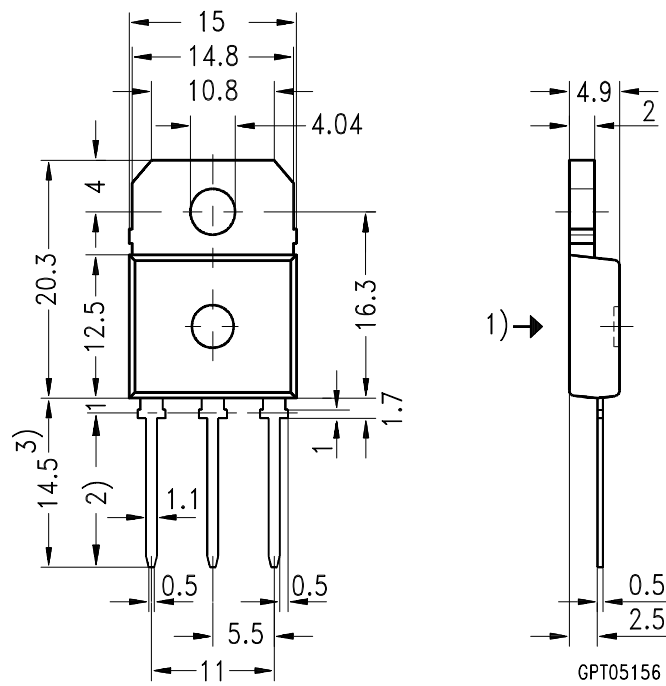




### Package Outlines

TO-218 AA

Dimension in mm



- 1) punch direction, burr max. 0.04
- 2) dip tinning
- 3) max. 15.5 by dip tinning press burr max. 0.05